

2N7000

Preferred Device

Small Signal MOSFET 200 mAmps, 60 Volts N-Channel TO-92

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS} V_{GSM}	± 20	Vdc
- Continuous - Non-repetitive ($t_p \leq 50 \mu\text{s}$)		± 40	Vpk
Drain Current	I_D I_{DM}	200	mA _{dc}
- Continuous - Pulsed		500	
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	T_L	300	$^\circ\text{C}$



ON Semiconductor®

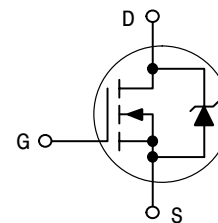
<http://onsemi.com>

200 mAmps

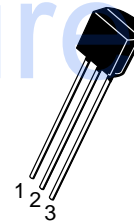
60 Volts

$R_{DS(on)} = 5 \Omega$

N-Channel

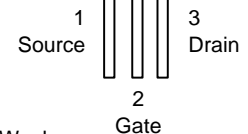


MARKING DIAGRAM & PIN ASSIGNMENT



TO-92
CASE 29
Style 22

2N7000
YWW



Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

2N7000

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)	V _{(BR)DSS}	60	–	Vdc
Zero Gate Voltage Drain Current (V _{DS} = 48 Vdc, V _{GS} = 0) (V _{DS} = 48 Vdc, V _{GS} = 0, T _J = 125°C)	I _{DSS}	–	1.0	μAdc mAdc
Gate–Body Leakage Current, Forward (V _{GSF} = 15 Vdc, V _{DS} = 0)	I _{GSSF}	–	–10	nAdc

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc)	V _{GS(th)}	0.8	3.0	Vdc
Static Drain–Source On–Resistance (V _{GS} = 10 Vdc, I _D = 0.5 Adc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc)	r _{DS(on)}	–	5.0 6.0	Ohm
Drain–Source On–Voltage (V _{GS} = 10 Vdc, I _D = 0.5 Adc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc)	V _{DS(on)}	–	2.5 0.45	Vdc
On–State Drain Current (V _{GS} = 4.5 Vdc, V _{DS} = 10 Vdc)	I _{d(on)}	75	–	mAdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAdc)	g _{fs}	100	–	μmhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	–	60	pF
Output Capacitance		C _{oss}	–	25	
Reverse Transfer Capacitance		C _{rss}	–	5.0	

SWITCHING CHARACTERISTICS (Note 1)

Turn–On Delay Time	(V _{DD} = 15 V, I _D = 500 mA, R _G = 25 Ω, R _L = 30 Ω, V _{gen} = 10 V)	t _{on}	–	10	ns
Turn–Off Delay Time		t _{off}	–	10	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N7000

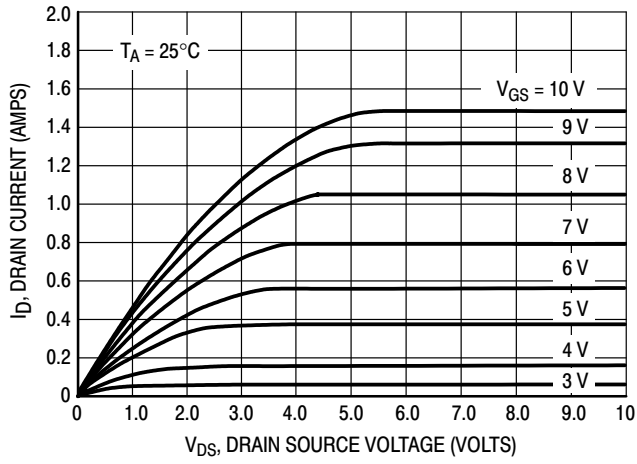


Figure 1. Ohmic Region

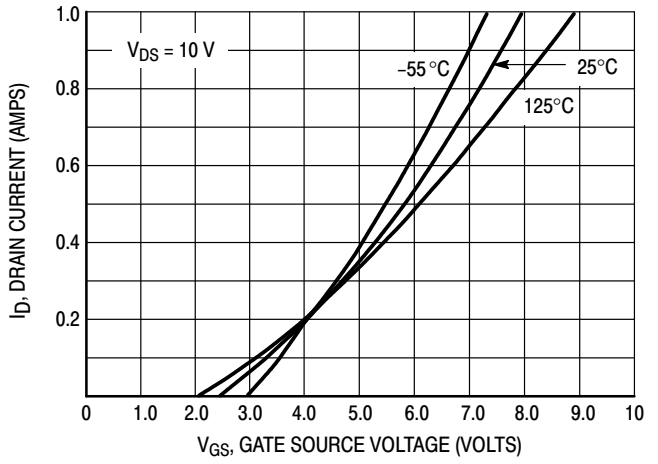


Figure 2. Transfer Characteristics

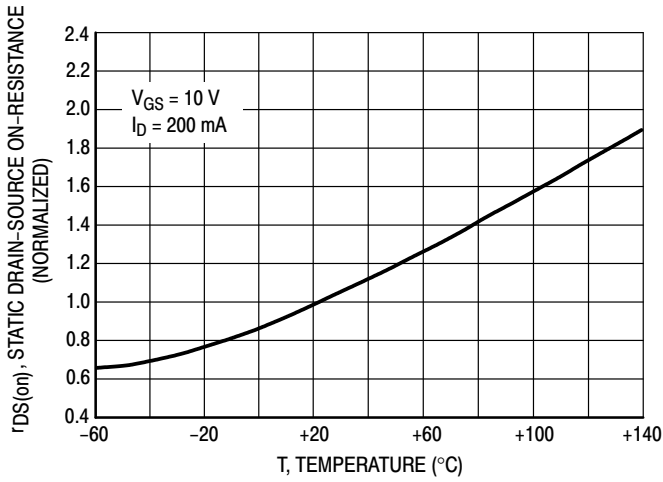


Figure 3. Temperature versus Static Drain-Source On-Resistance

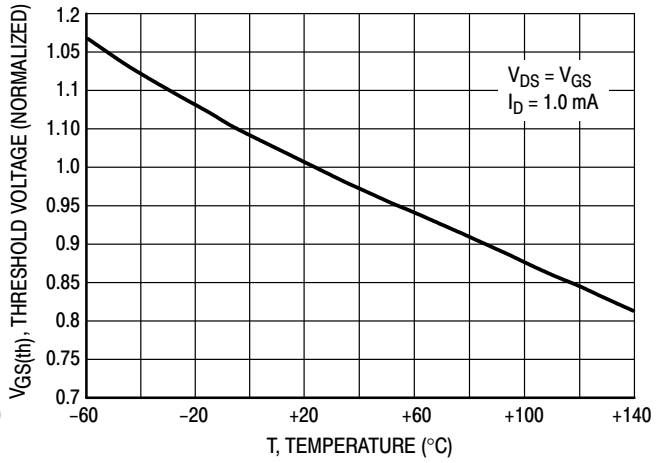


Figure 4. Temperature versus Gate Threshold Voltage

2N7000

ORDERING INFORMATION

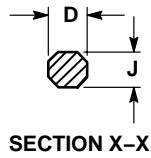
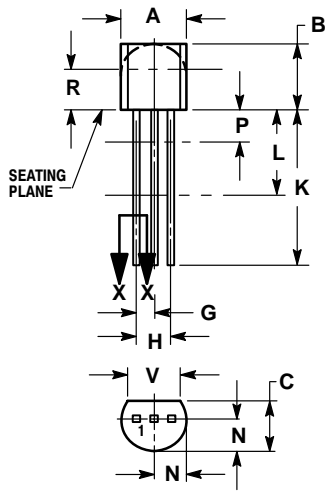
Device	Package	Shipping†
2N7000	TO-92	1000 Unit/Box
2N7000G	TO-92 (Pb-Free)	1000 Unit/Box
2N7000RLRA	TO-92	2000 Tape & Reel
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
2N7000RLRM	TO-92	2000 Ammo Pack
2N7000RLRMG	TO-92 (Pb-Free)	2000 Ammo Pack
2N7000RLRP	TO-92	2000 Ammo Pack
2N7000RLRPG	TO-92 (Pb-Free)	2000 Ammo Pack
2N7000ZL1	TO-92	2000 Ammo Pack
2N7000ZL1G	TO-92 (Pb-Free)	2000 Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2N7000

PACKAGE DIMENSIONS

TO-92
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 22:

- PIN 1. SOURCE
2. GATE
3. DRAIN

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center

2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051

Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your
local Sales Representative.